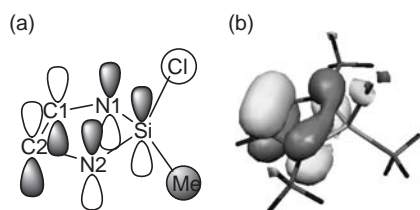


**Figure 2.** Molecular structure of  $3^+ \cdot \text{TPFPB}^- \cdot \text{CH}_2\text{Cl}_2$ . One of the disordered molecules is displayed at the 30% probability level. Hydrogen and solvent are omitted for clarity.



**Figure 3.** (a) Schematic representation of the  $\sigma_{(\text{Si-X})^*} - \pi$  interaction in **4**. (b) KS-HOMO of **4**.

**Table 1.** Bond lengths (Å), angles (deg), and other structural parameters for **3** and  $3^+$  by X-ray crystallography and for **4** and  $4^+$  by DFT calculations<sup>a</sup>

Compd	Si–N	C–N	C=C	$\Sigma_N^a$	$\Sigma_{\text{Ring}}^b$	$\theta^c$
<b>3</b>	1.729(2)	1.415(4)	1.320(4)	357.4(2)	539.8(2)	4.5(3)
	1.728(2)	1.412(4)		359.2(2)		3.9(3)
$3^+$	1.782(2)	1.336(4)	1.372(4)	359.2(2)	539.9(2)	0.7(3)
	1.780(2)	1.333(4)		360.0(2)		0.2(3)
<b>4</b>	1.738	1.414	1.350	357.9	538.8	9.8
$4^+$	1.798	1.347	1.406	359.9	540.0	2.1

<sup>a</sup>Ref. 14. <sup>b</sup>Sum of the angle around nitrogen. <sup>c</sup>Sum of the interior angles. <sup>d</sup>Dihedral angles of C1–N1–Si–N2 and N1–Si–N2–C2.

**3** into consideration (see below).

In order to examine the intrinsic electronic nature of DASCP, DFT calculations were conducted for neutral and radical cation states of a model compound **4**.<sup>14</sup> As shown in Table 1, the calculated result for DASCP **4** and its radical cation  $4^+$  reproduced the observed tendency for the structural change upon one-electron oxidation. In the HOMO of neutral **4**, the C=C and C–N bonds are in-phase and out-phase, respectively. Moreover, the rigidly fixed arrangement of exocyclic Si–C/Cl bonds is favorable for the in-phase  $\sigma_{(\text{Si-X})^*} - \pi$  ( $X = \text{C}, \text{Cl}$ ) interaction (Figure 3).<sup>15</sup> The elongation of C=C and Si–N bonds and shortening of the C–N bond upon one-electron oxidation of DASCP **3** can be explained by consideration of the phase of HOMO. Furthermore, this orbital interaction stabilizes the radical cation state of DASCP and planar structure of the five-membered ring in both the neutral and cation radical states.<sup>15</sup>

According to the above discussion, energy level of the HOMO in DASCP should be controlled by substituents on the silicon atom. For example, the energy level of the Kohn–Sham HOMO in dimethyl-DASCP **5** (–4.31 eV) becomes higher than that in chloro-DASCP **4** (–4.91 eV). Although the HOMO of

DASCPs is stabilized by the  $\sigma_{(\text{Si-X})^*} - \pi$  interaction, DASCP was found to have relatively high-lying HOMO. The results of the present study suggest that DASCP may be used as new functionality molecules such as hole-transport materials.

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- This is in sharp contrast to the formation of 2-silaimidazolium ion by chloride-ion abstraction upon treatment of **3** with  $\text{Et}_3\text{Si}^+ \text{TPFPB}^-$  (Ref. 6). The strong bond energy of Si–Cl (93.4 kcal mol<sup>-1</sup>) relative to that of C–Cl (78.0 kcal mol<sup>-1</sup>) should be one major reason.
- K. Ogawa, T. Kitagawa, S. Ishida, and K. Komatsu, submitted for publication.
- Anal. Calcd for  $\text{C}_{41}\text{H}_{39}\text{BClF}_{20}\text{N}_2\text{Si}_3$ : C, 46.01; H, 3.67; N, 2.62%. Found: C, 45.73; H, 3.75; N, 2.69%. The electronic spectrum in  $\text{CH}_2\text{Cl}_2$  displayed two broad bands at 418 nm (1500) and 322 nm (5200). According to TDDFT calculation of model compound  $4^+$ , these bands could be assigned to the HOMO  $\rightarrow$  SOMO and SOMO  $\rightarrow$  LUMO transitions, respectively.
- Computer simulations were performed using SimFonia software.
- Although there is some disorder around chlorine and bis(trimethylsilyl)methyl groups, (see supporting information) discussion on structural features of five-membered ring can be safely made. Crystal data for  $3^+ \cdot \text{TPFPB}^- \cdot \text{CH}_2\text{Cl}_2$ : FM =  $\text{C}_{42}\text{H}_{41}\text{BCl}_3\text{F}_{20}\text{N}_2\text{Si}_3$ , MW = 1155.2, monoclinic,  $a = 16.939(3)$ ,  $b = 17.258(3)$ ,  $c = 17.5640(18)$  Å,  $\beta = 102.831(7)^\circ$ ,  $V = 5006.3(13)$  Å<sup>3</sup>,  $P2_1/n$ ,  $Z = 4$ ,  $D_{\text{calcd}} = 1.533$  g/cm<sup>3</sup>,  $R = 0.0614$ ,  $wR_2 = 0.1229$ ,  $T = 100$  K, GOF = 1.026.
- Crystal data for **3**: FM =  $\text{C}_{17}\text{H}_{39}\text{ClN}_2\text{Si}_3$ , MW = 391.22, monoclinic,  $a = 11.6084(14)$ ,  $b = 11.1827(13)$ ,  $c = 17.954(2)$  Å,  $\beta = 90.219(2)^\circ$ ,  $V = 2330.7(5)$  Å<sup>3</sup>,  $P2_1/c$ ,  $Z = 4$ ,  $D_{\text{calcd}} = 1.115$  g/cm<sup>3</sup>,  $R = 0.0649$ ,  $wR_2 = 0.1354$ ,  $T = 100$  K, GOF = 1.054.
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